



**650V/ 10A Silicon Carbide Power Schottky Barrier Diode**

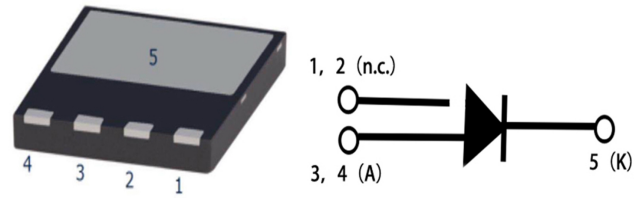
**Features**

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

Key Characteristics		
$V_{RRM}$	<b>650</b>	<b>V</b>
$I_F, T_c \leq 160^\circ\text{C}$	<b>10</b>	<b>A</b>
$Q_c$	<b>29</b>	<b>nC</b>

**Benefits**

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Bottom view

**Applications**

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



Part No.	Package Type	Marking
G4S06510QT	DFN8*8	G4S06510QT

**Maximum Ratings**

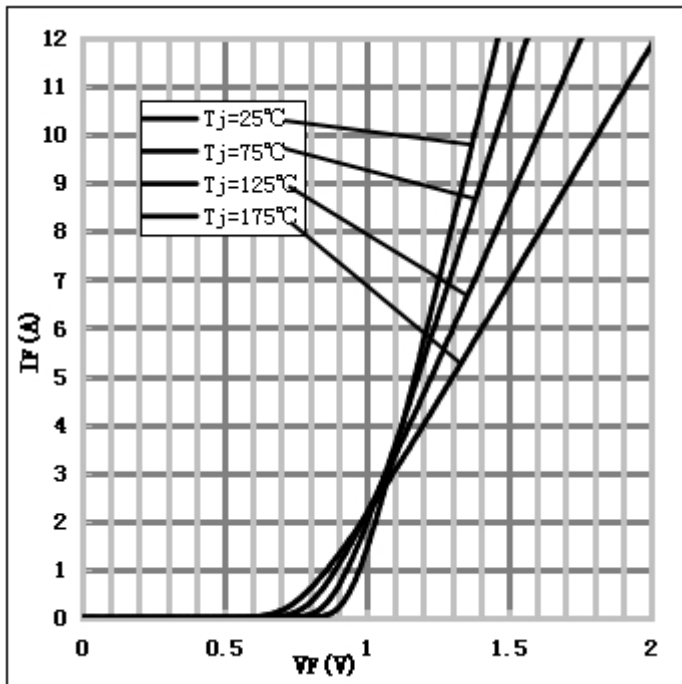
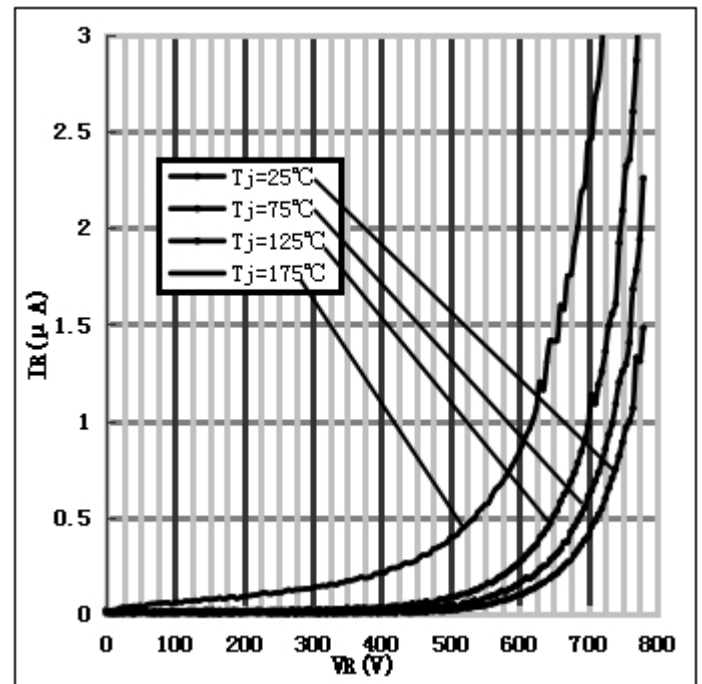
Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$		650	V
Surge Peak Reverse Voltage	$V_{RSM}$		650	V
DC Blocking Voltage	$V_{DC}$		650	V
Continuous Forward Current	$I_F$	$T_C=25^{\circ}C$	44.9	A
		$T_C=125^{\circ}C$	24.1	
		$T_C=160^{\circ}C$	10	
Repetitive Peak Forward Surge Current	$I_{FRM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave, $D=0.3$	40	A
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave	105	A
Power Dissipation	$P_{TOT}$	$T_C=25^{\circ}C$	238	W
		$T_C=110^{\circ}C$	103	W
Operating Junction	$T_j$		-55°C to 175°C	°C
Storage Temperature	$T_{stg}$		-55°C to 175°C	°C

**Thermal Characteristics**

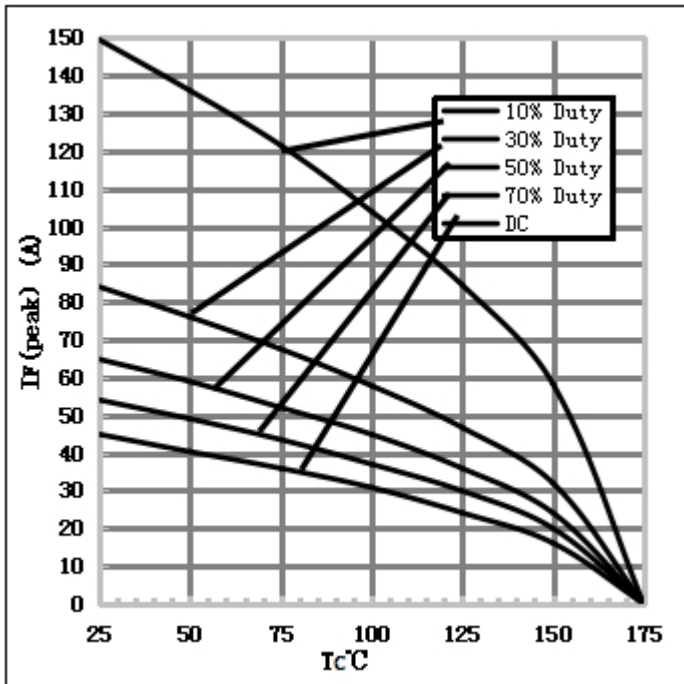
Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{thJC}$		0.63	°C/W

Electrical Characteristics

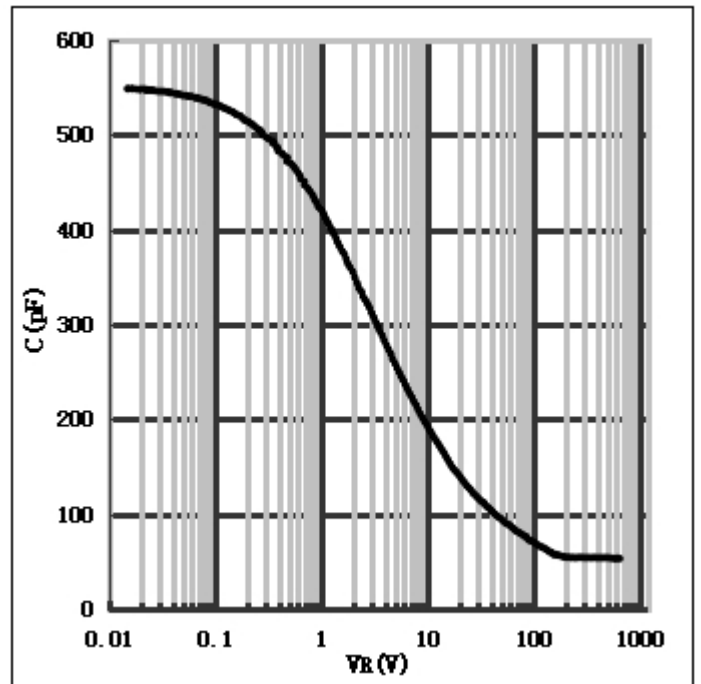
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	$V_F$	$I_F=10A, T_j=25^\circ C$	1.38	1.7	V
		$I_F=10A, T_j=175^\circ C$	1.82	2.5	
Reverse Current	$I_R$	$V_R=650V, T_j=25^\circ C$	0.25	50	$\mu A$
		$V_R=650V, T_j=175^\circ C$	1.5	100	
Total Capacitive Charge	$Q_C$	$V_R=400V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$	29	-	nC
Total Capacitance	C	$V_R=0V, T_j=25^\circ C, f=1MHz$	550	588	pF
		$V_R=200V, T_j=25^\circ C, f=1MHz$	60	65	
		$V_R=400V, T_j=25^\circ C, f=1MHz$	59	61	

Performance Graphs1) Forward IV characteristics as a function of  $T_j$  :2) Reverse IV characteristics as a function of  $T_j$  :

3) Current Derating:

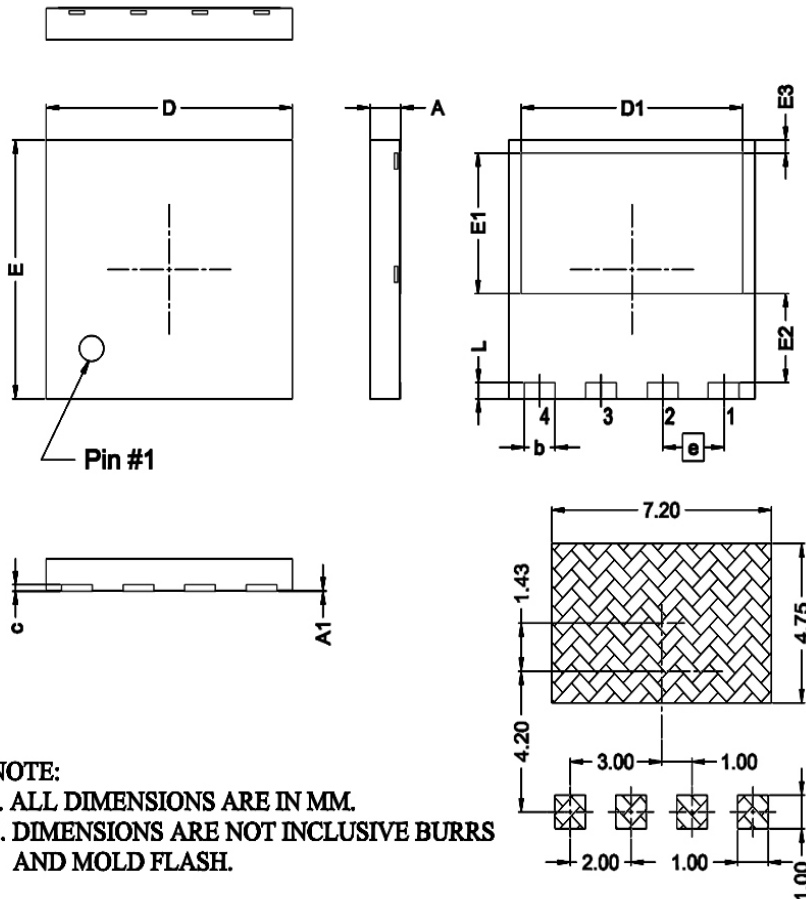


4) Capacitance vs. reverse voltage:



Package DFN8\*8

单位: mm



NOTE:  
 1. ALL DIMENSIONS ARE IN MM.  
 2. DIMENSIONS ARE NOT INCLUSIVE BURRS AND MOLD FLASH.

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	—	0.05
b	0.90	1.00	1.10
c	0.10	0.20	0.30
D	7.90	8.00	8.10
D1	7.10	7.20	7.30
E	7.90	8.00	8.10
E1	4.25	4.35	4.45
E2	2.65	2.75	2.85
E3	0.30	0.40	0.50
e	2.00 BSC		
L	0.40	0.50	0.60

Land Pattern

**Note:** The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: <http://globalpowertech.cn/English/index.asp>

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